



ISSN No. : 2321-9653

IJRASET

**International Journal for Research in Applied
Science & Engineering Technology**

IJRASET is indexed with Crossref for DOI-DOI : 10.22214

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Effect of Doping Concentration on Electrical Parameter of Tri-Gate Junctionless N-
channel FinFET*

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Volume 9, Issue II, February 2021
in*

*International Journal for Research in Applied Science &
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